

TO-92L Plastic-Encapsulate Transistors

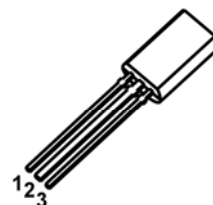
KTA1024 TRANSISTOR (PNP)

FEATURES

- High Voltage : $V_{CE0} = -150V$.
- Low Output Capacitance : $C_{ob} = 5.0pF$ (Max.).
- High Transition frequency : $f_T = 120MHz$ (Typ.).
- Complementary to KTC3206.

TO-92L

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS ($T_a = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-50	mA
P_C	Collector Power Dissipation	0.75	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55-150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -150V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -10mA$	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.8	V
Base -emitter voltage	V_{BE}	$V_{CE} = -5V, I_C = -30mA$			-0.9	V
Transition frequency	f_T	$V_{CE} = -30V, I_C = -10mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		4.0	5.0	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240